

1SS368

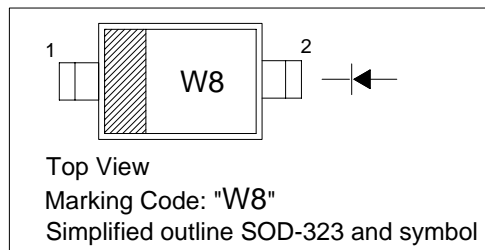
SILICON EPITAXIAL PLANAR DIODE Ultra High Speed Switching Application

Features

- Small package
- Low forward voltage:
 $V_F=0.98V$ (typ.)
- Fast reverse recovery time:
 $t_{rr}=1.6ns$ (typ.)
- Small total capacitance:
 $C_T=0.5pF$ (typ.)

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



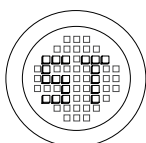
Absolute Maximum Ratings (T_j = 25°)

Parameter	Symbol	Value	Unit
Maximum (peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum (peak) Forward Current	I_{FM}	200	mA
Average Forward Current	I_O	100	mA
Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150 ¹⁾	mW
Junction Temperature	T_J	125	°
Storage Temperature Range	T_s	-55 to +125	°

1) Mounted on a glass epoxy circuit board of 20x20mm, pad dimension of 4x4mm.

Characteristics at T_j = 25 °

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 1mA$	V_F	-	0.62	-	V
	$I_F = 10mA$	V_F	-	0.75	-	V
	$I_F = 100mA$	V_F	-	0.98	1.20	V
Reverse Current	$V_R = 30V$	I_R	-	-	0.1	μA
	$V_R = 80V$	I_R	-	-	0.5	μA
Total Capacitance	$f = 1MHz$	C_T	-	0.5	3.0	pF
Reverse Recovery Time	$I_F = 10mA$	t_{rr}	-	1.6	4.0	ns



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РАДИОТЕХ

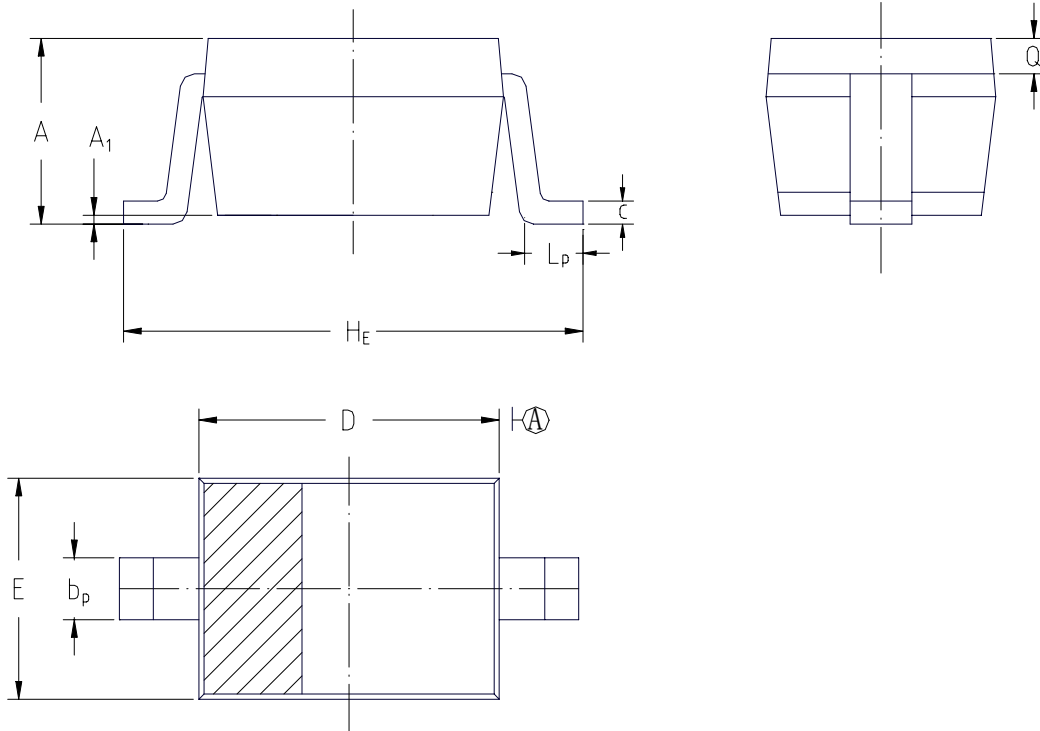
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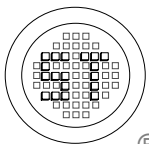
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	A ₁	b _p	c	D	E	H _E	L _p	Q
mm	1.10 0.80	0.1 0	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30	0.50 0.10	0.15 REF.



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 550159-04-002-04

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